PROCESS CP617

Small Signal Transistor

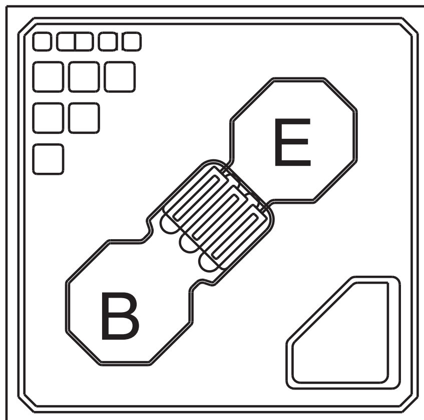
PNP - Silicon RF Transistor Chip

Central™ Semiconductor Corp.

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	16 x 16 MILS
Die Thickness	8.0 MILS
Base Bonding Pad Area	3.75 x 3.75 MILS
Emitter Bonding Pad Area	3.75 x 3.75 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 10,000Å

GEOMETRY



BACKSIDE COLLECTOR R0

GROSS DIE PER 4 INCH WAFER

44,140

PRINCIPAL DEVICE TYPES

CM4957

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centralsemi.com

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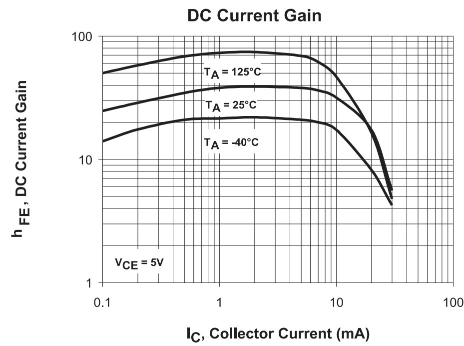
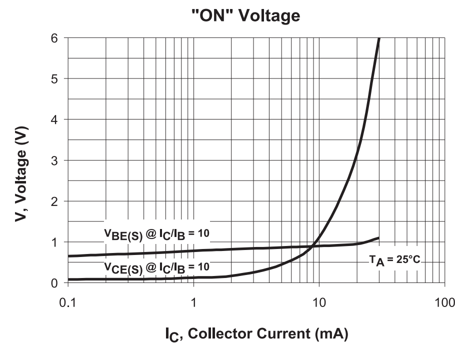
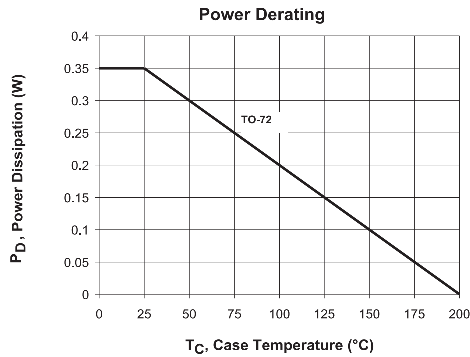
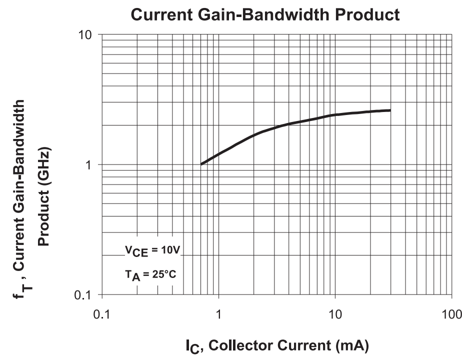
PROCESS CP617

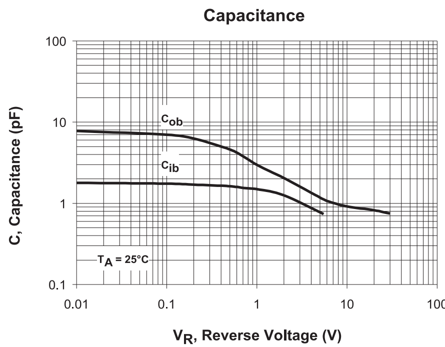
Typical Electrical Characteristics











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